

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-61 (Canceled).

62. (Currently Amended) A nitride semiconductor light emitting device comprising;

a substrate,

a first nitride semiconductor layer having an impurity concentration within $1 \times 10^{17}/\text{cm}^3$, said first nitride semiconductor layer being a single layer,

a second nitride semiconductor layer having an n-type electrode, said second nitride semiconductor layer being a single layer,

a third nitride semiconductor layer having an impurity concentration within $1 \times 10^{17}/\text{cm}^3$, said third nitride semiconductor layer being a super lattice layer of InGaN layers and GaN layers, and

an active layer where electrons and holes are combined.

63. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer is made of GaN or AlGaN and said second nitride semiconductor layer includes Si as an n-type impurity.

64. (Previously Presented) The nitride semiconductor light emitting device

according to claim 62;

wherein said first nitride semiconductor layer is made of GaN or AlGaN.

65. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer has an carrier concentration more than $3 \times 10^{18}/\text{cm}^3$.

66. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer has a resistivity less than $8 \times 10^{-3} \text{ ohm} \cdot \text{cm}$.

67. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

further comprising a buffer layer between said substrate and said first nitride semiconductor layer.

68. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said first nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm .

69. (Previously Presented) The nitride semiconductor light emitting device according to claim 62;

wherein said second nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm ,

70. (Currently Amended) A nitride semiconductor light emitting device comprising:

a substrate,

a first nitride semiconductor layer having an impurity concentration within $1 \times 10^{17}/\text{cm}^3$, said first nitride semiconductor layer being a single layer,

a second nitride semiconductor layer having an n-type electrode, said second nitride semiconductor layer being a single layer,

~~a third nitride semiconductor layer having an impurity concentration within $1 \times 10^{17}/\text{cm}^3$, said third nitride semiconductor layer being a super lattice layer of GaN layers, and~~

an active layer where electrons and holes are combined.

71. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer is made of GaN or AlGaN and said second nitride semiconductor layer includes Si as an n-type impurity.

72. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said first nitride semiconductor layer is made of GaN or AlGaN

73. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has an carrier concentration more than $3 \times 10^{18}/\text{cm}^3$.

74. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has a resistivity less than $8 \times 10^{-3} \text{ ohm} \cdot \text{cm}$.

75. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

further comprising a buffer layer between said substrate and said first nitride semiconductor layer.

76. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said first nitride semiconductor layer has a thickness within

a range of from 0.1 to 20 μm ,

77. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said second nitride semiconductor layer has a thickness within a range of from 0.1 to 20 μm .

78. (Previously Presented) The nitride semiconductor light emitting device according to claim 70;

wherein said third nitride semiconductor layer being a super lattice layer of undoped GaN layers and Si doped GaN layers.

79. (New) The nitride semiconductor light emitting device according to claim 78;

wherein said Si doped GaN layers are doped with Si to $1 \times 10^{19}/\text{cm}^3$.

80. (New) The nitride semiconductor light emitting device according to claim 78;

wherein said undoped GaN layers have a thickness of 75Å and Si doped GaN layers have a thickness of 25Å.

81. The nitride semiconductor light emitting device according to claim 78;

wherein said third nitride semiconductor layer has a thickness of 600Å